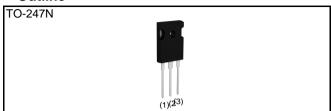
## Datasheet



## N-channel SiC power MOSFET

V <sub>DSS</sub>	750V
R <sub>DS(on)</sub> (Typ.)	26mΩ
I <sub>D</sub> *1	56A
$P_D$	176W

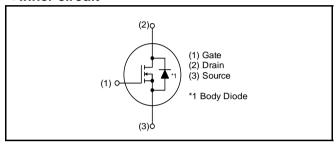
#### Outline



#### Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

#### •Inner circuit



## Application

- · Solar inverters
- DC/DC converters
- · Switch mode power supplies
- · Induction heating

#### Packaging specifications

	Packing	Tube
	Reel size (mm)	ı
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Taping code	C11
	Marking	SCT4026DE

## ● **Absolute maximum ratings** (T<sub>vj</sub> = 25°C unless otherwise specified.)

Parameter		Symbol	Value	Unit	
Drain - source voltage		$V_{DSS}$	750	V	
Continuous drain	\/ - \/	$T_c = 25^{\circ}C$	I <sub>D</sub> , I <sub>S</sub> *1	56	А
and source current	$V_{GS} = V_{GS\_on}$	T <sub>c</sub> = 100°C	ID, IS	39	А
Pulsed drain current	$V_{GS} = V_{GS\_on}$	$T_c = 25^{\circ}C$	I <sub>D,pulse</sub> *2	91	А
Body diode pulsed forward	ard current	$T_c = 25^{\circ}C$	I <sub>S,pulse</sub> *1,*3	56	А
Body diode surge forward current $V_{GS} = 0$		$V_{GS} = 0 V$	I <sub>S,pulse</sub> *1,*4	91	А
Gate - source voltage (DC)		$V_{GSS\_DC}$	-4 to +21	V	
Gate - source surge voltage (t <sub>surge</sub> < 300ns)		V <sub>GSS_surge</sub> *5	-4 to +23	V	
Recommended turn-on gate - source drive voltage		ive voltage	$V_{GS\_on}^{*6}$	+15 to +18	V
Recommended turn-off gate - source drive voltage		$V_{GS\_off}$	0	V	
Virtual junction temperature		$T_{vj}$	175	°C	
Range of storage temper	erature		$T_{stg}$	-40 to +175	°C

# ullet Electrical characteristics (T<sub>vj</sub> = 25°C unless otherwise specified)

Parameter	Symbol Conditions —		Values			Unit
raiailletei			Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	W	$V_{GS} = 0 \text{ V}, I_D = 9.2 \text{mA}$				V
	V (BR)DSS	$T_{vj} = 25^{\circ}C$	750	-	-	V
		$V_{GS} = 0 \text{ V}, V_{DS} = 750 \text{V}$				
Zero Gate voltage Drain current	I <sub>DSS</sub>	$T_{vj} = 25^{\circ}C$	-	1	80	μΑ
Diam current		T <sub>vj</sub> = 150°C	-	10	-	
Gate - Source leakage current	I <sub>GSS+</sub>	$V_{GS} = +21V , V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current		$V_{GS} = -4V$ , $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_{D} = 15.4 \text{mA}$	2.8	ı	4.8	V
		$V_{GS} = 18V, I_{D} = 29A$				
Static Drain - Source on - state resistance	R <sub>DS(on)</sub> *8	$T_{vj} = 25^{\circ}C$	-	26	34	mΩ
on state registance		T <sub>vj</sub> = 150°C	-	44	-	
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	1	-	Ω

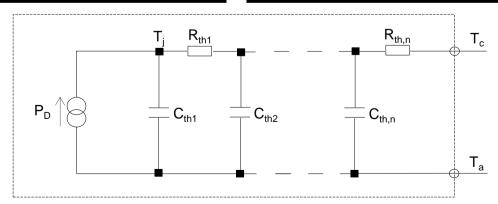
## ●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R <sub>thJC</sub> *9	-	0.65	0.85	K/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	4.9 <b>×</b> 10 <sup>-2</sup>	
R <sub>th2</sub>	3.0 ×10 <sup>-1</sup>	K/W
R <sub>th3</sub>	3.0 ×10 <sup>-1</sup>	

Symbol	Value	Unit
C <sub>th1</sub>	8.7 ×10 <sup>-4</sup>	
$C_{th2}$	4.0 <b>×</b> 10 <sup>-3</sup>	Ws/K
C <sub>th3</sub>	5.2 ×10 <sup>-2</sup>	



# ullet Electrical characteristics (T<sub>vj</sub> = 25°C unless otherwise specified)

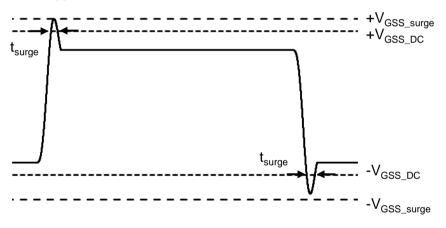
Davamatav	Cymah al	Conditions		Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	g <sub>fs</sub> *8	$V_{DS} = 10V, I_{D} = 29A$	-	16	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	2320	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 500V	-	111	-	pF
Reverse transfer capacitance	$C_{rss}$	f = 1MHz	-	9	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 500V$	-	143	-	pF
Total Gate charge	Q <sub>g</sub> *8	$V_{DS} = 500V$ $I_{D} = 29A$	-	94	-	
Gate - Source charge	Q <sub>gs</sub> *8	$V_{GS} = 18V$	ı	20	ı	nC
Gate - Drain charge	Q <sub>gd</sub> *8	See Fig. 1-1, 1-2.	-	23	-	
Turn - on delay time	t <sub>d(on)</sub> *8	$V_{DS} = 500V$ $I_{D} = 29A$	ı	10	ı	
Rise time	t <sub>r</sub> *8	$V_{GS} = +18V / 0V$	1	39	1	ns
Turn - off delay time	t <sub>d(off)</sub> *8	$R_G = 6.8\Omega$ , L = 250 $\mu$ H $E_{on}$ includes diode	ı	44	ı	115
Fall time	t <sub>f</sub> *8	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	1	16	1	
Turn - on switching loss	E <sub>on</sub> *8	See Fig. 2-1, 2-2, 2-3.	-	460	-	μJ
Turn - off switching loss	E <sub>off</sub> *8		ı	120	ı	μυ
$V_{GS(on)} = +15V$ Short-circuit	• t <sub>sc</sub> *9	V <sub>DS</sub> ≤ 400V V <sub>DS,peak</sub> ≤ 750V	-	12.0	-	μs
withstand time $V_{GS(on)} = +18V$	'sc	$T_{vj(start)} = 25^{\circ}C$ $R_G = 2.2\Omega$	-	11.5	-	μs

# ●Body diode electrical characteristics (Source-Drain) (T<sub>vi</sub> = 25°C unless otherwise specified)

Darameter	Cymbal	Conditions	Values			l lmit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	V <sub>SD</sub> *8	$V_{GS} = 0V, I_{S} = 29A$	-	3.3	ı	V
Reverse recovery time	t <sub>rr</sub> *8	$I_F = 29A$ $V_R = 500V$	ı	19	ı	ns
Reverse recovery charge	Q <sub>rr</sub> *8	di/dt = 1500A/µs	-	100	-	nC
Peak reverse recovery current	I <sub>rrm</sub> *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	ı	11	1	Α

<sup>\*1</sup> Limited by maximum  $T_{vj}$  and for Max.  $R_{thJC}$ .

## \*5 Example of acceptable V<sub>GS</sub> waveform



- \*6 Please be advised not to use SiC-MOSFETs with V<sub>GS</sub> below 10V as doing so may cause thermal runaway.
- \*7 Tested after applying  $V_{GS} = 21V$  for 100ms.
- \*8 Pulsed
- \*9 The value is based on TO-247 package. Single Pulsed.
- \*10 Measured conformable to JESD51-14.

See the application note "rthjc\_measurement\_and\_usage\_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc\_measurement\_and\_usage\_an-e.pdf

<sup>\*2</sup> Pulse width and duty cycle are limited by  $T_{v_j,max}$ .

<sup>\*3</sup> Only for body-diode, Repititive pulse, PW ≤ 1.5µs, Duty cycle ≤ 5%

<sup>\*4</sup> When used as a protective function, PW ≤ 10µs

Fig.1 Power Dissipation Derating Curve

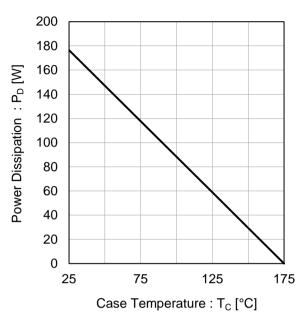


Fig.2 Maximum Safe Operating Area

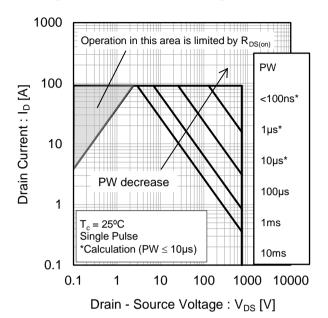
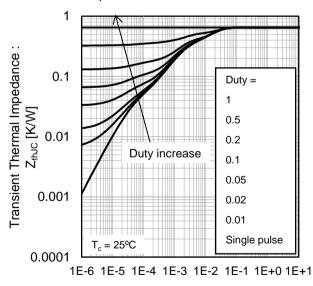


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



Pulse Width: PW [s]

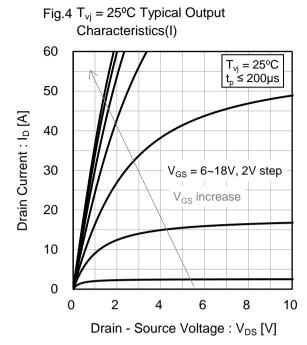
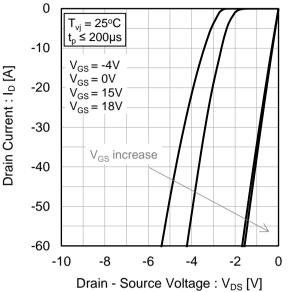
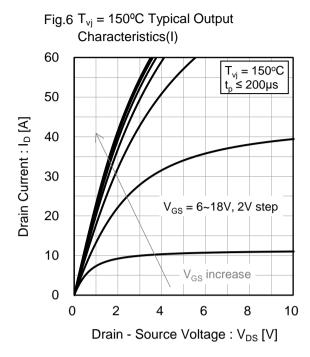
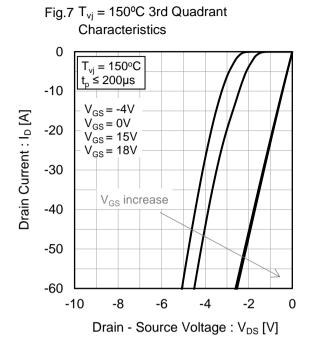


Fig.5  $T_{vj} = 25^{\circ}C$  3rd Quadrant Characteristics







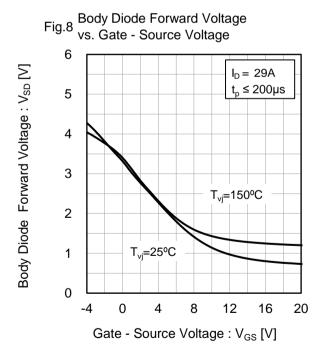


Fig.9 Typical Transfer Characteristics (I)

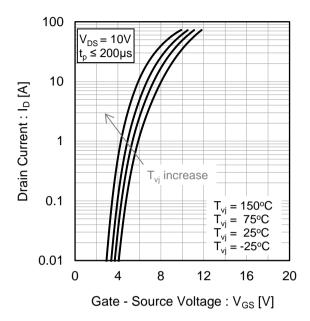


Fig.10 Typical Transfer Characteristics (II)

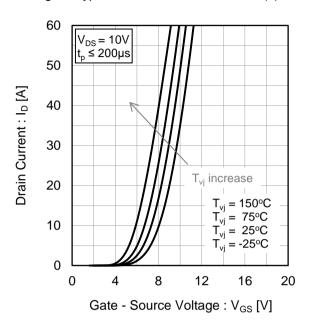


Fig.11 Gate Threshold Voltage vs. Virtual Junction Temperature

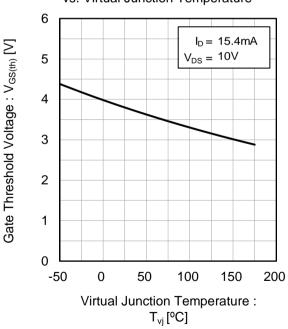
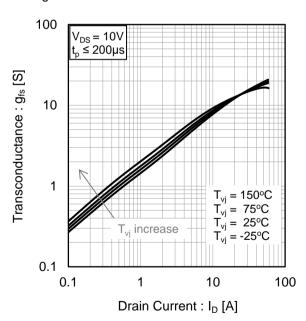
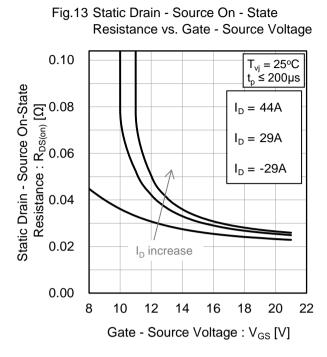


Fig.12 Transconductance vs. Drain Current





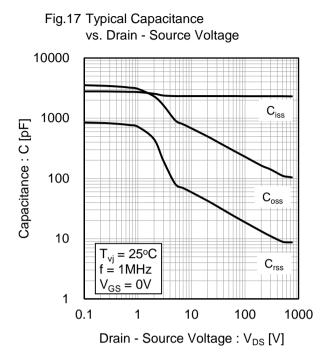
Resistance vs. Virtual Junction Temperature 0.10  $V_{GS} = 18V$  $t_p \le 200 \mu s$ Static Drain - Source On-State Resistance :  $R_{DS(on)}$  [ $\Omega$ ] 80.0 90.0 90.0  $I_D = 44A$  $I_{D} = 29A$  $I_{D} = -29A$ I<sub>D</sub> increase 0.02 0.00 0 -50 50 100 150 200 Virtual Junction Temperature: T<sub>vi</sub> [°C]

Fig.14 Static Drain - Source On - State

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current = 150°C = 125°C Static Drain - Source On-State  $T_{vj} = 75^{\circ}C$ = 25°C Resistance: R<sub>DS(on)</sub> [Ω] = -25°C 0.1 0.01  $T_{vj}$  increase  $V_{GS} = 18V$  $t_p \le 200 \mu s$ 0.001 10 100 Drain Current: I<sub>D</sub> [A]

Fig.16 Normalized Drain - Source Breakdown Voltage vs. Virtual Junction Temperature 1.1 Normalized Drain - Source **Breakdown Voltage** 1.0  $V_{GS} = 0 V$  $I_D = 9.2 \text{ mA}$ 0.9 0 100 150 -50 50 200 Virtual Junction Temperature : T<sub>vi</sub> [°C]

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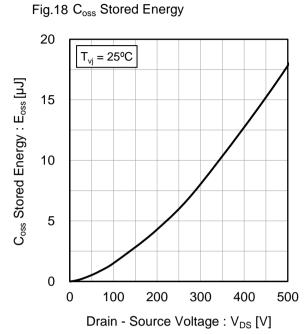


Fig.19 Dynamic Input Characteristics

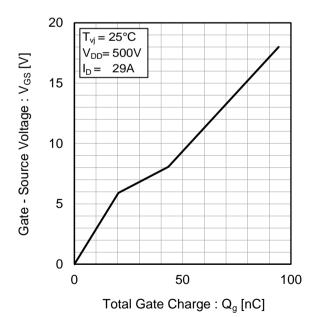


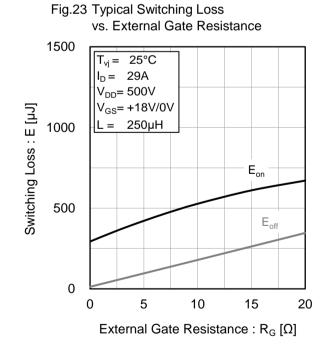
Fig.20 Typical Switching Time vs. External Gate Resistance 120  $T_{vi} = 25^{\circ}C$ 29A 100 V<sub>DD</sub>= 500V V<sub>GS</sub>= +18V/0V t<sub>d(off)</sub> Switching Time:t [ns] 80  $L = 250 \mu H$ 60  $t_{\rm r}$ 40 20  $\mathsf{t}_\mathsf{f}$ 0 5 10 15 20

External Gate Resistance :  $R_G[\Omega]$ 

vs. Drain - Source Voltage 1500  $T_{v_i} = 25^{\circ}C$  $I_D =$ 29A V<sub>GS</sub>= +18V/0V Switching Loss: E [µJ]  $R_G = 6.8\Omega$ 1000  $L = 250 \mu H$ 500  $\mathsf{E}_{\mathsf{on}}$  $\mathsf{E}_{\mathsf{off}}$ 0 200 100 300 400 500 Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.21 Typical Switching Loss

Fig.22 Typical Switching Loss vs. Drain Current 1500  $T_{vj} =$ 25°C V<sub>DD</sub>= 500V  $V_{GS}$ = +18V/0V  $R_G = 6.8\Omega$ Switching Loss: E [µJ] 250µH 1000  $\mathsf{E}_{\mathsf{on}}$ 500  $\mathsf{E}_{\mathsf{off}}$ 0 0 20 40 60 Drain Current: I<sub>D</sub> [A]



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#### Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

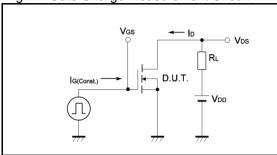


Fig.2-1 Switching Characteristics Measurement Circuit

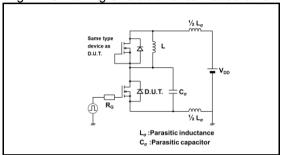


Fig.2-3 Waveforms for Switching Energy Loss

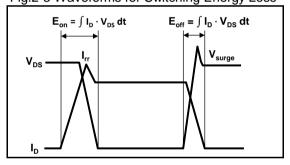


Fig.3-1 Reverse Recovery Time Measurement Circuit

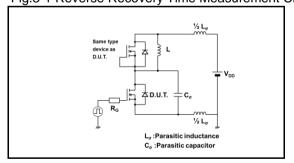


Fig.1-2 Gate Charge Waveform

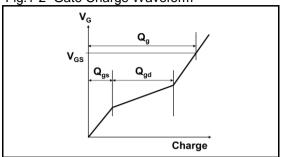


Fig.2-2 Waveforms for Switching Time

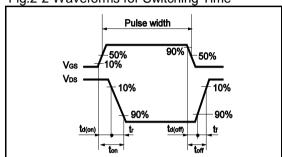
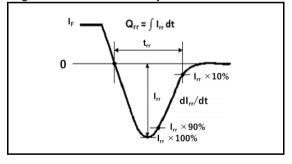
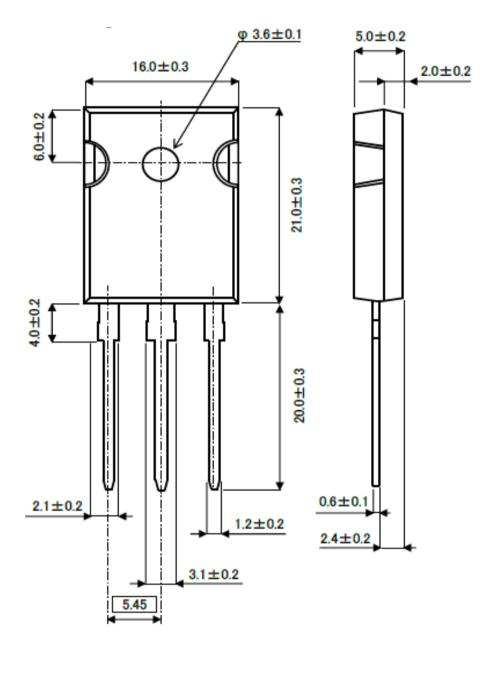


Fig.3-2 Reverse Recovery Waveform

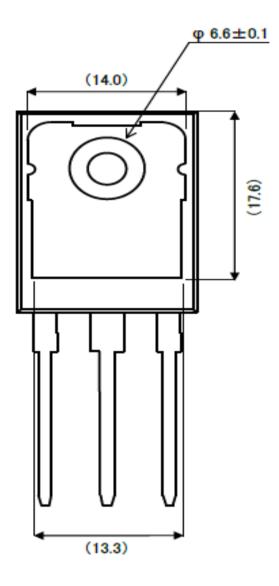


# ●Package Dimensions



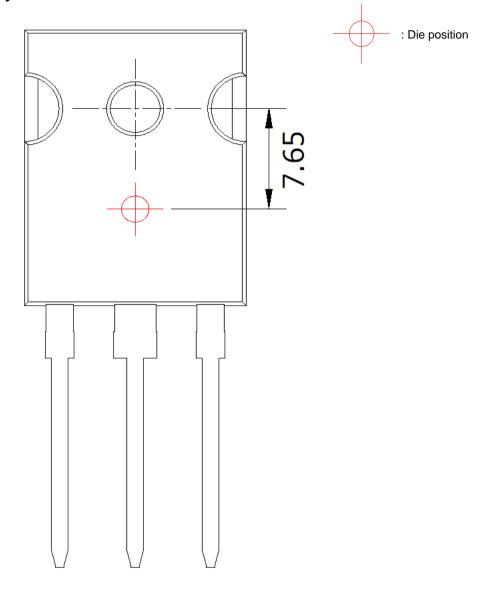


Unit: mm



Unit: mm

# **●**Die Bonding Layout



- •Front view of the packaging.
- •Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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